

东莞市华远电子有限公司

DONG GUAN SHI HUA YUAN ELECTRON CO..LTD.

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TO-220 Plastic-Encapsulate Transistors

2SD880 TRANSISTOR (NPN)

FEATURES

Power dissipation

P_{CM} : 1.5 W (Tamb=25)

Collector current

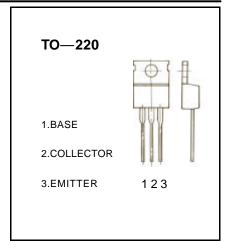
 I_{CM} : 3 A

Collector-base voltage

 $V_{(BR)CBO}$: 60 V

Operating and storage junction temperature range

 T_J , T_{stg} : -55 to +150



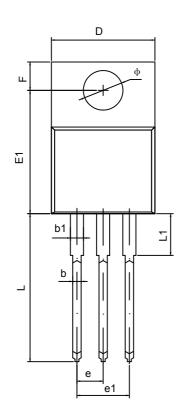
ELECTRICAL CHARACTERISTICS (Tamb=25 unless otherwise specified)

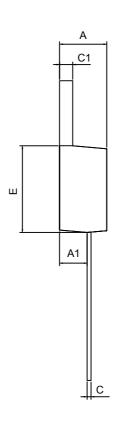
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR) _{CBO}	lc=100μA,l _E =0	60			V
Collector-emitter breakdown voltage	V(BR) _{CEO}	Ic=50mA,I _B =0				V
Emitter-base breakdown voltage	V(BR) _{EBO}	I _E = 100μΑ,I _C =0	7			V
Collector cut-off current	I _{CBO}	$V_{CB}=60V,I_{E}=0$			100	μΑ
Emitter cut-off current	I _{EBO}	V _{EB} =7V,I _C =0			100	μΑ
DC current gain	h _{FE}	V _{CE} =5V,I _C =500mA 6			300	
Collector-emitter saturation voltage	V _{CE} (sat)	I _C =3A,I _B =300mA			1	V
Base-emitter saturation voltage	V_{BE}	I _C =0.5A, V _{CE} = 5V			1	V
Transition Frequency	f _T	V _{CE} =5 V, I _C =500mA		3		MHz
Collector output capacitance	C_ob	V _{CE} =10V,I _E =0,f=1MHz		70		pF
Turn on time	t _{on}			0.8		μs
Storage time	t _s	I _{B1} =-I _{B2} =0.2A, I _C =2A V _{CC} =30V,PW=20µs		1.5		μs
Fall time	t _f			0.8		μs

CLASSIFICATION OF hFE

Rank	0	Y	GR
Range	60-120	100-200	150-300

TO-220-3L PACKAGE OUTLINE DIMENSIONS





Symbol	Dimensions I	n Millimeters	Dimensions In Inches		
	Min	Max	Min	Max	
Α	4.470	4.670	1.176	0.184	
A1	2.520	2.820	0.099	0.111	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.310	0.530	0.012	0.021	
c1	1.710	1.370	0.046	0.054	
D	10.010	10.310	0.394	0.406	
E	8.500	8.900	0.335	0.350	
E1	12.060	12.460	0.475	0.491	
е	2.540TYP		0.100TYP		
e1	4.980	5.180	0.196	0.204	
F	2.590	2.890	0.102	0.114	
L	13.400	13.800	0.528	0.543	
L1	3.560	3.960	0.140	0.156	
ф	3.790	3.890	0.149	0.153	